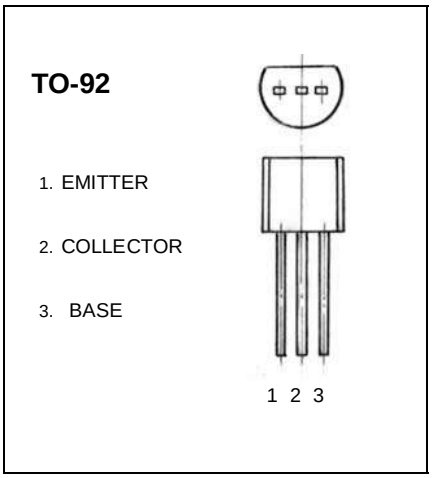
TO-92 Plastic-Encapsulated Transistors

2SA1625 TRANSISTOR (PNP)



FEATURES

Power dissipation

P_{CM} : 750 mW (Tamb=25℃)

Collector current

I_{CM} : -0.5 A

Collector-base voltage

$V_{(BR)CBO}$: -400 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	Ic=-100μA, I_E=0	-400			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	Ic=-1mA, I_B=0	-400			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-100μA, I_C=0	-7			V
Collector cut-off current	I_{CBO}	V_{CB}=-400V, I_E=0			-1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-5V, I_C=0			-1	μA
DC current gain	$h_{FE(1)}$	V_{CE}=-5V, I_C=-50mA	40		200	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-100mA, I_B=-10mA			-1	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=-100mA, I_B=-10mA			-1.2	V
Transition frequency	f_T	V_{CE}=-10V, I_C=-10mA		10		MHz
Collector output capacitance	C_{ob}	V_{CB}=-10V, I_E=0, f=1MHz	20	40		pF
Turn-on Time	t_{on}	V_{CC}=-150V, I_c=-100mA, $I_{B!}$=I_{B2}-10mA, RL=1.5KΩ		1		μs
Storage Time	t_{stg}			5		μs
Fall-Time	t_f			1		μs

CLASSIFICATION OF $h_{FE(1)}$

Rank	M	L	K
Range	40-80	60-120	100-200